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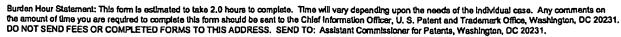
Complete If Known				
Application Number	10/616,603			
Filing Date	10 July 2003			
First Named Inventor	Christophe Pierrat et al.			
Group Art Unit				
Examiner Name				
Attorney Docket Number	FTIS 1001-1			

ſ	U.S. PATENT DOCUMENTS						
Examiner Initials	Cite No.1	Mumbor	ment Code ² nown)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Cotumns, Lines, Where Relevant Passages or Relsvant Figures Appeer	
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Examiner Initiats*	Cite No.1	tnotude name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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